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June 2014

FDA20N50F

N-Channel UniFETTM FRFET[®] MOSFET 500 V, 22 A, 260 m Ω

Features

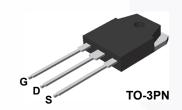
- $R_{DS(on)}$ = 220 m Ω (Typ.) @ V_{GS} = 10 V, I_{D} = 11 A
- Low Gate Charge (Typ. 50 nC)
- Low C_{rss} (Typ. 27 pF)
- · 100% Avalanche Tested
- · Improved dv/dt Capability
- · RoHS Compliant

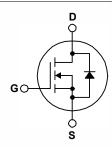
Applications

- PDP TV
- · Uninterruptible Power Supply
- · AC-DC Power Supply

Description

UniFETTM MOSFET is Fairchild Semiconductor's high voltage MOSFET family based on planar stripe and DMOS technology. This MOSFET is tailored to reduce on-state resistance, and to provide better switching performance and higher avalanche energy strength. The body diode's reverse recovery performance of UniFET FRFET® MOSFET has been enhanced by lifetime control. Its trr is less than 100nsec and the reverse dv/dt immunity is 15V/ns while normal planar MOSFETs have over 200nsec and 4.5V/nsec respectively. Therefore, it can remove additional component and improve system reliability in certain applications in which the performance of MOSFET's body diode is significant. This device family is suitable for switching power converter applications such as power factor correction (PFC), flat panel display (FPD) TV power, ATX and electronic lamp ballasts.





MOSFET Maximum Ratings T_C = 25°C unless otherwise noted.

| Symbol | | Parameter | | FDA20N50F | Unit | |
|-----------------------------------|--|---------------------------------------|----------|-------------|------|--|
| V _{DSS} | Drain to Source Voltage | | | 500 | V | |
| V _{GSS} | Gate to Source Voltage | | | ±30 | V | |
| | Drain Current | - Continuous (T _C = 25°C) | | 22 | Δ. | |
| ID | Diamounent | - Continuous (T _C = 100°C) | | 13 | Α | |
| I _{DM} | Drain Current | - Pulsed | (Note 1) | 88 | Α | |
| E _{AS} | Single Pulsed Avalanche E | nergy | (Note 2) | 1110 | mJ | |
| I _{AR} | Avalanche Current | | (Note 1) | 22 | Α | |
| E _{AR} | Repetitive Avalanche Ener | gy | (Note 1) | 39 | mJ | |
| dv/dt | Peak Diode Recovery dv/d | t | (Note 3) | 20 | V/ns | |
| D | Dawer Dissipation | (T _C = 25°C) | | 388 | W | |
| P_{D} | Power Dissipation | - Derate above 25°C | | 3.1 | W/°C | |
| T _J , T _{STG} | Operating and Storage Ter | nperature Range | | -55 to +150 | °C | |
| T _L | Maximum Lead Temperatu 1/8" from Case for 5 Secon | • • | | 300 | °C | |

Thermal Characteristics

| Symbol | Parameter | FDA20N50F | Unit |
|-----------------|---|-----------|-------|
| $R_{\theta JC}$ | Thermal Resistance, Junction to Case, Max. | 0.44 | °C/W |
| $R_{\theta JA}$ | Thermal Resistance, Junction to Ambient, Max. | 40 | *C/VV |

Package Marking and Ordering Information

| Device Marking | Device | Package | Reel Size | Tape Width | Quantity |
|----------------|-----------|---------|-----------|------------|----------|
| FDA20N50F | FDA20N50F | TO-3PN | Tube | N/A | 30 units |

Electrical Characteristics $T_C = 25^{\circ}C$ unless otherwise noted.

| Symbol | Parameter | lest Conditions | win. | ıyp. | wax. | Unit |
|---|--|--|------|------|------|------|
| Off Charac | cteristics | | | | | |
| BV _{DSS} | Drain to Source Breakdown Voltage | $I_D = 250\mu A, V_{GS} = 0V, T_J = 25^{\circ}C$ | 500 | - | - | V |
| ΔBV _{DSS} / ΔΤ _J | Breakdown Voltage Temperature Coefficient | I _D = 250μA, Referenced to 25°C | - | 0.6 | - | V/°C |
| I | Zero Gate Voltage Drain Current | $V_{DS} = 500V, V_{GS} = 0V$ | - | - | 10 | μА |
| IDSS | Zero Gate Voltage Drain Current | $V_{DS} = 400V, T_{C} = 125^{\circ}C$ | - | - | 100 | μΑ |
| I_{GSS} | Gate to Body Leakage Current | $V_{GS} = \pm 30V, V_{DS} = 0V$ | - | - | ±100 | nA |

On Characteristics

| V _{GS(th)} | Gate Threshold Voltage | $V_{GS} = V_{DS}, I_D = 250 \mu A$ | 3.0 | - | 5.0 | V |
|---------------------|--------------------------------------|---|-----|------|------|---|
| R _{DS(on)} | Static Drain to Source On Resistance | V _{GS} = 10V, I _D = 11A | - | 0.22 | 0.26 | Ω |
| 9 _{FS} | Forward Transconductance | V _{DS} = 40V, I _D = 11A | - | 24 | - | S |

Dynamic Characteristics

| C _{iss} | Input Capacitance | V - 25V V - 0V | - | 2550 | 3390 | pF |
|---------------------|-------------------------------|---|-------|------|------|----|
| C _{oss} | Output Capacitance | $V_{DS} = 25V, V_{GS} = 0V$ f = 1MHz | | 350 | 465 | pF |
| C _{rss} | Reverse Transfer Capacitance | 1 - 1WH12 | - \ | 27 | 40 | pF |
| Q _{g(tot)} | Total Gate Charge at 10V | | - | 50 | 65 | nC |
| Q_{gs} | Gate to Source Gate Charge | $V_{DS} = 400V, I_{D} = 20A$ | - | 14 | - | nC |
| Q_{gd} | Gate to Drain "Miller" Charge | V _{GS} = 10V (No | te 4) | 20 | - | nC |

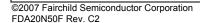
Switching Characteristics

| t _{d(on)} | Turn-On Delay Time | | - | 45 | 100 | ns |
|---------------------|---------------------|----------------------------|-----|-----|-----|----|
| t _r | Turn-On Rise Time | $V_{DD} = 250V, I_D = 20A$ | - | 120 | 250 | ns |
| t _{d(off)} | Turn-Off Delay Time | $R_G = 25\Omega$ | - | 100 | 210 | ns |
| t _f | Turn-Off Fall Time | (Note 4) | - / | 60 | 130 | ns |

Drain-Source Diode Characteristics

| I _S | Maximum Continuous Drain to Source Diode Forward Current | | | - | 22 | Α |
|-----------------|--|---|---|-----|-----|----|
| I _{SM} | Maximum Pulsed Drain to Source Diode Forward Current | | | - | 88 | Α |
| V_{SD} | Drain to Source Diode Forward Voltage | $V_{GS} = 0V, I_{SD} = 22A$ | - | - | 1.5 | V |
| t _{rr} | Reverse Recovery Time | V _{GS} = 0V, I _{SD} = 20A | - | 154 | - | ns |
| Q _{rr} | Reverse Recovery Charge | dI _F /dt = 100A/μs | - | 0.5 | - | μС |

- $\label{eq:Notes:Notes:Notes:} \begin{tabular}{ll} \textbf{Notes:} \\ 1: & \textbf{Repetitive Rating: Pulse width limited by maximum junction temperature} \\ 2: & \textbf{L} = 5\text{mH, I}_{AS} = 20\text{A, V}_{DD} = 50\text{V, R}_{G} = 25\Omega, \textbf{Starting T}_{J} = 25^{\circ}\text{C} \\ 3: & \textbf{I}_{SD} \leq 22\text{A, di/dt} \leq 200\text{A/µs, V}_{DD} \leq \text{BV}_{DSS}, \textbf{Starting T}_{J} = 25^{\circ}\text{C} \\ 4: & \textbf{Essentially Independent of Operating Temperature Typical Characteristics} \\ \end{tabular}$



Typical Characteristics

Figure 1. On-Region Characteristics

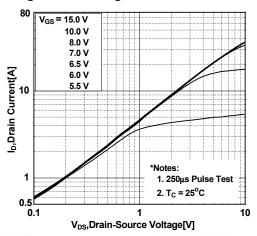


Figure 3. On-Resistance Variation vs.
Drain Current and Gate Voltage

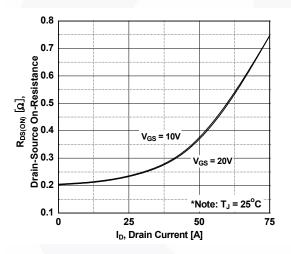


Figure 5. Capacitance Characteristics

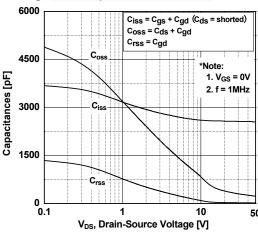


Figure 2. Transfer Characteristics

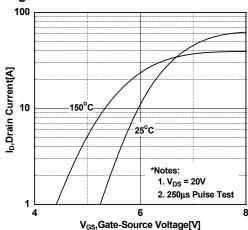


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature

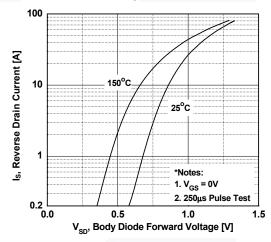
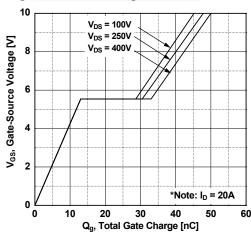


Figure 6. Gate Charge Characteristics



Typical Characteristics (Continued)

Figure 7. Breakdown Voltage Variation vs. Temperature

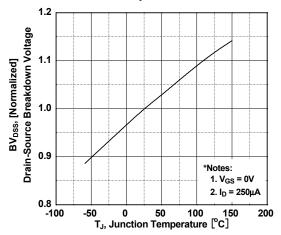


Figure 9. Maximum Drain Current vs. Case Temperature

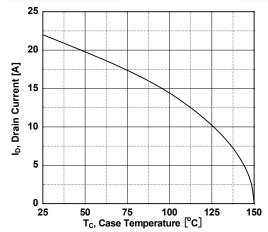


Figure 8. Maximum Safe Operating Area

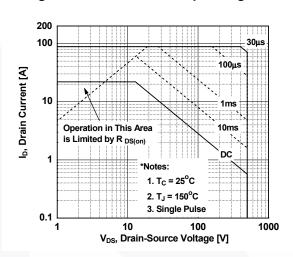
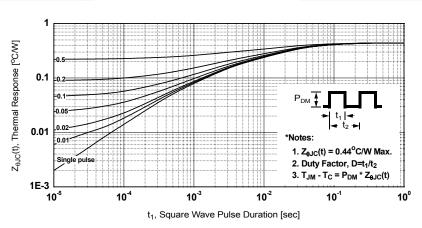


Figure 10. Transient Thermal Response Curve



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Figure 11. Gate Charge Test Circuit & Waveform

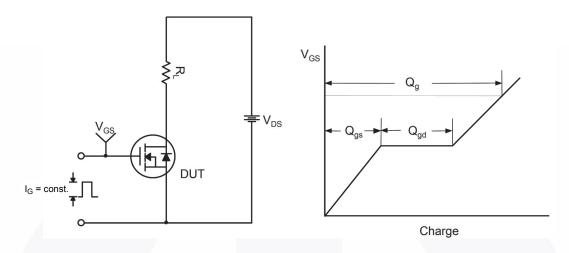


Figure 12. Resistive Switching Test Circuit & Waveforms

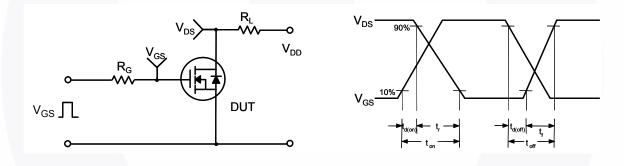
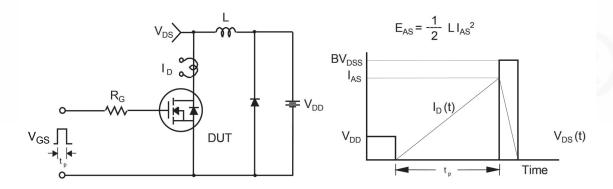


Figure 13. Unclamped Inductive Switching Test Circuit & Waveforms



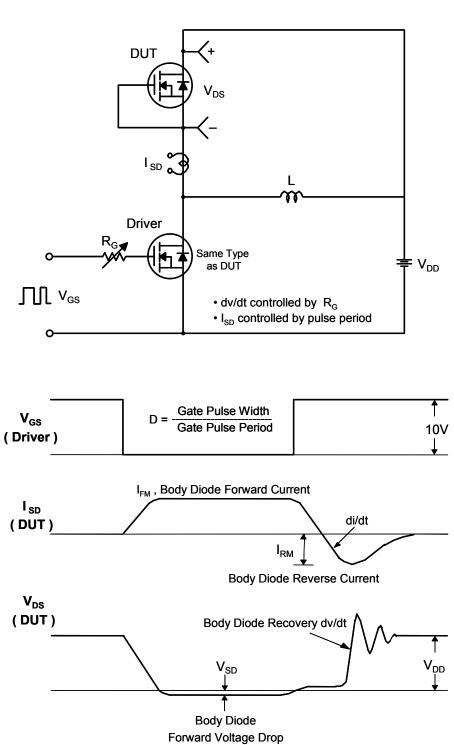
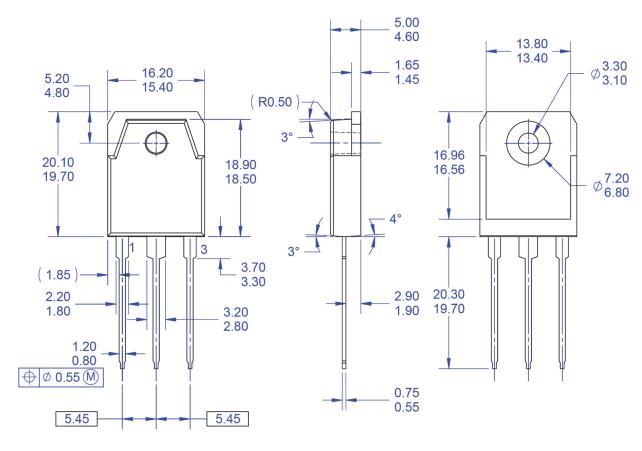
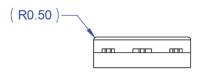


Figure 14. Peak Diode Recovery dv/dt Test Circuit & Waveforms

Mechanical Dimensions





NOTES: UNLESS OTHERWISE SPECIFIED

- A) THIS PACKAGE CONFORMS TO EIAJ SC-65 PACKAGING STANDARD.
- ALL DIMENSIONS ARE IN MILLIMETERS.
- **DIMENSION AND TOLERANCING PER** ASME14.5-2009.
- D) DIMENSIONS ARE EXCLUSSIVE OF BURRS, MOLD FLASH, AND TIE BAR EXTRUSSIONS.
 E) DRAWING FILE NAME: TO3PN03AREV1.
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Figure 15. TO3PN, 3-Lead, Plastic, EIAJ SC-65

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